

SCT2750NY

N-channel SiC power MOSFET

V _{DSS}	1700V
R _{DS(on)} (Typ.)	$750 m\Omega$
I _D	6A
P _D	57W

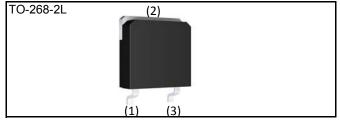
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Long creepage distance with no center lead
- 4) Simple to drive
- 5) Pb-free lead plating ; RoHS compliant

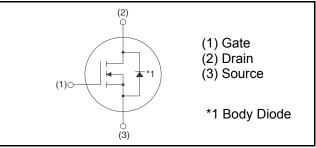
Application

- Auxilialy power supplies
- •Switch mode power supplies

Outline



Inner circuit



Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Tuno	Tape width (mm)	24
Туре	Basic ordering unit (pcs)	400
	Taping code	ТВ
	Marking	SCT2750NY

●Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V _{DSS}	1700	V
Continuous drain surrant	$T_c = 25^{\circ}C$	I _D ^{*1}	5.9	А
Continuous drain current	T _c = 100°C	I _D ^{*1}	4	А
Pulsed drain current		I _{D,pulse} ^{*2}	14	А
Gate - Source voltage (DC)		V _{GSS}	-6 to 22	V
Gate - Source surge voltage (t _{surge} <300nsec)		V _{GSS_surge} *3	-10 to 26	V
Power dissipation ($T_c = 25^{\circ}C$)		P _D	57	W
Junction temperature		Tj	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

•Thermal resistance

Parameter	Symbol		Unit		
Farantelei	Symbol	Min.	Тур.	Max.	Onit
Thermal resistance, junction - case	R _{thJC}	-	2.04	2.65	°C/W

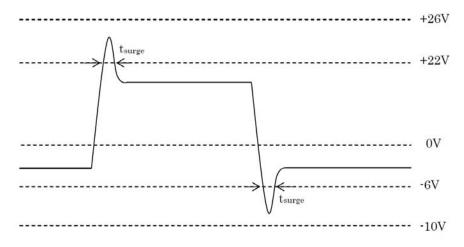
•Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit	
Faranieter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain - Source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 1mA	1700	-	-	V	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 1700V, V_{GS} = 0V$ $T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$	-	0.1 0.2	10 -	μA	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA	
Gate - Source leakage current	I _{GSS-}	V_{GS} = -6V, V_{DS} = 0V	-	-	-100	nA	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 0.63 \text{mA}$	1.6	2.8	4.0	V	

*1 Limited only by maximum temperature allowed.

*2 PW \leq 10 $\mu s,$ Duty cycle \leq 1%

*3 Example of acceptable Vgs waveform



*4 Pulsed

•Electrical characteristics ($T_a = 25^{\circ}C$)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Onit
		V _{GS} = 18V, I _D = 1.7A				
Static drain - source on - state resistance	R _{DS(on)} *4	T _j = 25°C	-	750	975	mΩ
		T _j = 125°C	-	1088	-	
Gate input resistance	R _G	f = 1MHz, open drain	-	49	-	Ω
Transconductance	g _{fs} *4	V _{DS} = 10V, I _D = 1.7A	-	0.6	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	275	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	19	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	7	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V V _{DS} = 0V to 800V	-	21	-	pF
Turn - on delay time	t _{d(on)} *4	V _{DD} = 500V, I _D = 1.7A	-	19	-	
Rise time	t _r *4	V _{GS} = 18V/0V	-	24	-	20
Turn - off delay time	t _{d(off)} *4	R _L = 294Ω	-	41	-	ns
Fall time	t _f *4	$R_{G} = 0\Omega$	-	63	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 800V, I_{D} = 1.7A$ $V_{GS} = 18V/0V$	-	76	-	
Turn - off switching loss	E _{off} *4	R _G = 0Ω, L=2mH *E _{on} includes diode reverse recovery	-	33	-	μJ

●Gate Charge characteristics (T_a = 25°C)

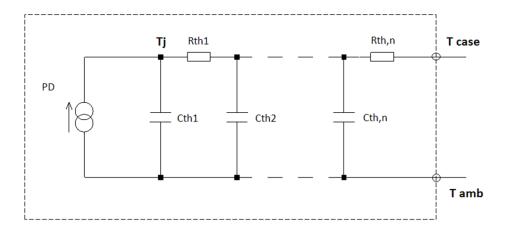
Parameter	Symbol	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Total gate charge	Q_g^{*4}	V _{DD} = 500V	-	17	-		
Gate - Source charge	Q _{gs} ^{*4}	I _D = 1.5A	-	5	-	nC	
Gate - Drain charge	Q_{gd}^{*4}	V _{GS} = 18V	-	6.5	-		
Gate plateau voltage	V _(plateau)	$V_{DD} = 500V, I_D = 1.5A$	-	11.0	-	V	

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions		Values		
Faranielei	Symbol	Conditions	Min.	Тур.	Max.	Unit
Inverse diode continuous, forward current	ا _S *1	T _c = 25°C	-	-	5.9	А
Inverse diode direct current, pulsed	I _{SM} *2	T _c - 20 0	-	-	14	А
Forward voltage	V_{SD} *4	V _{GS} = 0V, I _S = 1.7A	-	4.3	-	V
Reverse recovery time	t _{rr} *4		-	26	-	ns
Reverse recovery charge	Q _{rr} ^{*4}	I _F = 1.7A, V _R = 800V di/dt = 290A/μs	-	18	-	nC
Peak reverse recovery current	^{*4}		-	1.3	-	А

•Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R _{th1}	243m		C_{th1}	352µ	
R _{th2}	1529m	K/W	C _{th2}	1.57m	Ws/K
R _{th3}	268m		C_{th3}	68.7m	



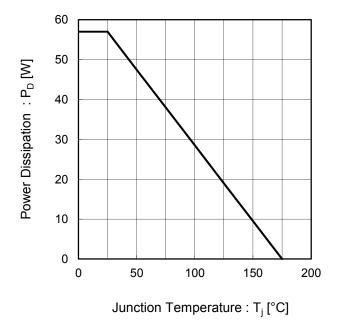
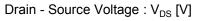


Fig.1 Power Dissipation Derating Curve

100 Operation in this area is limited P_w = 100μs by R_{DS(on)} 10 Drain Current : I_D [A] P_w = 1ms $P_W = 10ms$ 1 0.1 P_w = 100ms T_a = 25°C Single Pulse 0.01 0.1 1 10 100 1000 10000

Fig.2 Maximum Safe Operating Area



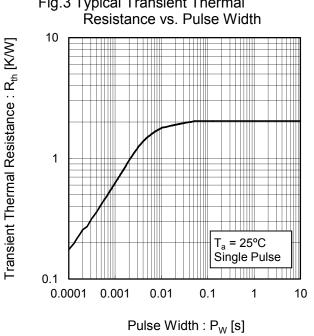


Fig.3 Typical Transient Thermal

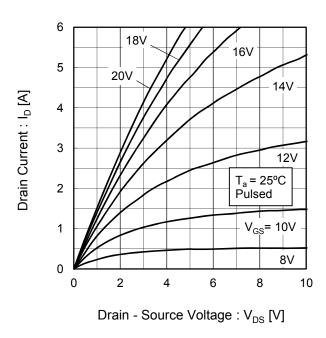
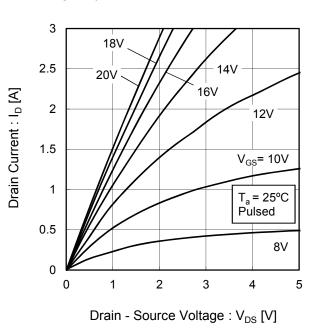
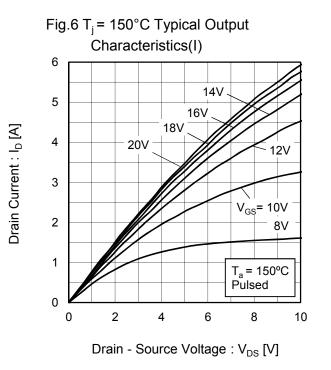
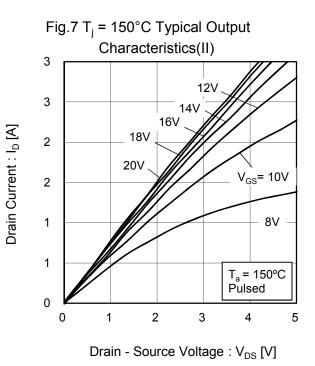


Fig.4 Typical Output Characteristics(I)

Fig.5 Typical Output Characteristics(II)







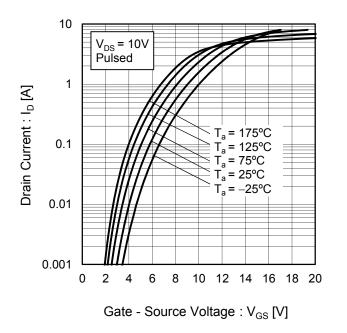
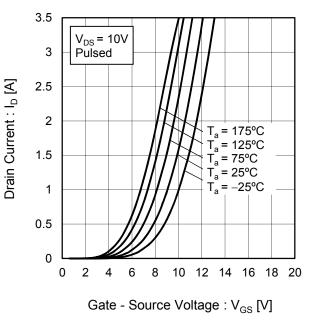


Fig.8 Typical Transfer Characteristics (I)

Fig.9 Typical Transfer Characteristics (II)



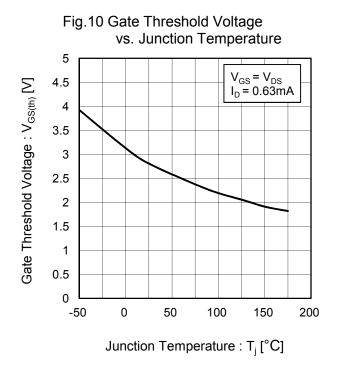
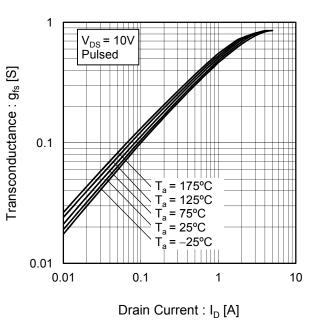


Fig.11 Transconductance vs. Drain Current



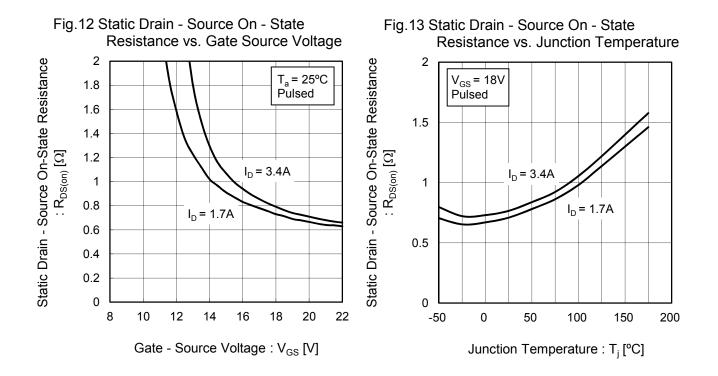


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current Static Drain - Source On-State Resistance 10 : R_{DS(on)} [Ω] 1 T_a = 175°C T_a^a = 125°C T_a = 75°C T_{a} V_{GS} = 18V T_a = 25°C Pulsed T_a[−] = −25°C 0.1 0.1 1 10

Drain Current : I_D [A]

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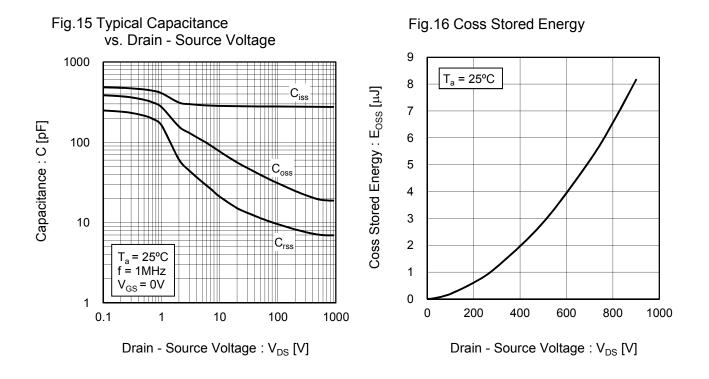
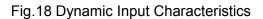
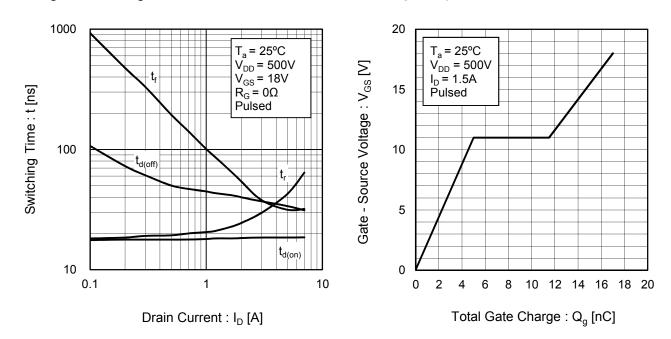
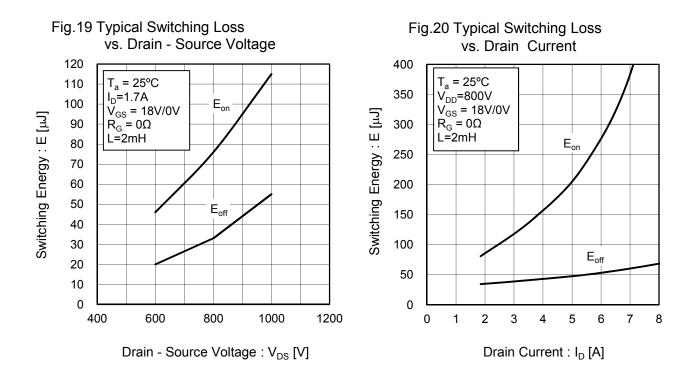


Fig.17 Switching Characteristics







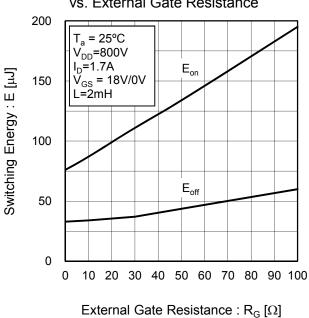
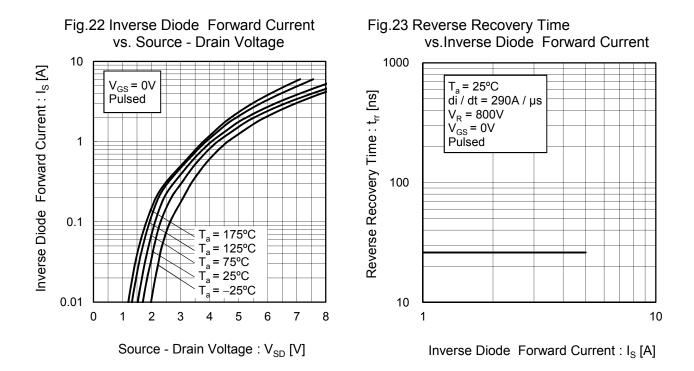


Fig.21 Typical Switching Loss vs. External Gate Resistance





Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

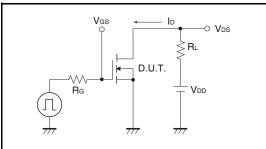


Fig.2-1 Gate Charge Measurement Circuit

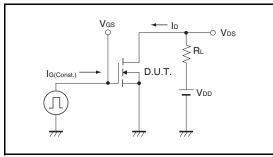


Fig.3-1 Switching Energy Measurement Circuit

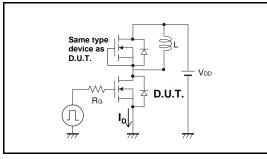


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

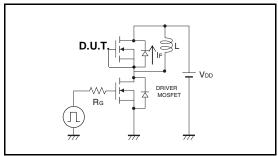


Fig.1-2 Switching Waveforms

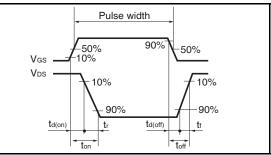


Fig.2-2 Gate Charge Waveform

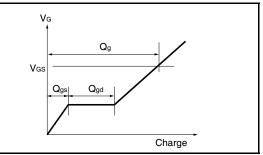
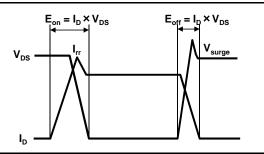
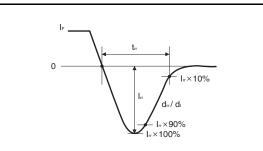


Fig.3-2 Switching Waveforms







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